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Supporting Information

SiCO Ceramics as Storage Materials for Alkali Metals/Ions: Insights on Structure Moieties from Solid-State NMR and DFT Calculations

Edina Šić, Jochen Rohrer,* Emmanuel III Ricohermoso, Karsten Albe, Emmanuel Ionescu, Ralf Riedel, Hergen Breitzke, Torsten Gutmann,* and Gerd Buntkowsky* This publication is part of a joint Special Collection of ChemSusChem, Batteries & Supercaps, and Energy Technology including invited contributions focusing on the “International Conference on Sodium Batteries (ICNaB)”. Please visit [to view all contributions.](#) © 2023 The Authors. ChemSusChem published by Wiley-VCH GmbH. This is an open access article under the terms of the Creative Commons Attribution Non-Commercial NoDerivs License, which permits use and distribution in any medium, provided the original work is properly cited, the use is non-commercial and no modifications or adaptations are made.

Elemental Analysis

The elemental composition of each sample was determined via the hot gas extraction method. A carbon analyzer (CS 800, Eltra GmbH, Neuss, Germany) was used to measure the content of carbon by detecting and quantifying the oxidized carbon species using IR spectroscopy. The oxygen content was quantified using a nitrogen/oxygen analyzer (Leco TC-436, Leco Corporation, Michigan, US).

sample	Volume in %			Element Content in wt %		
	SiO ₂	SiC	Free Carbon	Si	O	C
SiCO-C14%	76.75	12.24	11.01	46.65	39.4	13.95
SiCO-C24%	54.49	27.83	17.68	49.13	26.44	24.43
SiCO-C36%	51.19	11.66	36.43	36.53	27.9	35.57
SiCO-C55%	30.19	12.28	57.53	27.96	16.93	55.11

Results of NMR deconvolution

sample	shift/width	Si-species			
		SiO ₄	SiCO ₃	SiC ₂ O ₂	SiC ₄
SiCO-C14%	δ (ppm)	-104.5	-73	-40	-
	fwhm (ppm)	22	22	33	-
SiCO-C24%	δ (ppm)	-99.55	-68.84	-36.37	-17
	fwhm (ppm)	17	27.56	24.8	15.5
SiCO-C36%	δ (ppm)	-106	-75	-37.12	-
	fwhm (ppm)	24	28.8	25.48	-
SiCO-C55%	δ (ppm)	-99	-71	-39	-18
	fwhm (ppm)	24	26	34	15

Table S3. The semi-quantitative estimation of the $\text{SiC}_x\text{O}_{4-x}$ -fractions achieved applying the line deconvolution of the Hahn-echo ^{29}Si MAS NMR data of the SiOC-PDCs presented in the manuscript in Figure 3b).

Si-species in %				
sample	SiO_4	SiCO_3	SiC_2O_2	SiC_4
SiCO-C14%	51	38	11	-
SiCO-C24%	15	40	34	11
SiCO-C36%	68	28	4	-
SiCO-C55%	21	35	39	5

Table S4. Fit data for the ^{29}Si CPMAS NMR spectra of the SiOC-PDCs with carbon content between 14-55 % provided in the manuscript in Figure 3c).

sample	shift/width	Si-species				
		SiO_4	SiCO_3	SiC_2O_2	SiC_4	SiC_3O
SiCO-C14%	δ (ppm)	-109.68	-71.60	-31.90	-16	-7.3
	fwhm (ppm)	20.66	22	21	43	19
SiCO-C24%	δ (ppm)	-106.5	-71.9	-34.06	-17.5	-7.8
	fwhm (ppm)	29	23	23	45	23
SiCO-C36%	δ (ppm)	-104.06	-74.40	-38.70	-16.62	-5
	fwhm (ppm)	28.49	26.42	23.71	26.63	30.30
SiCO-C55%	δ (ppm)	-102.64	-70.91	-35.74	-17.83	-7.06
	fwhm (ppm)	28.96	23.8	21.99	48.59	17.64

Table S5. Percentages of the $\text{SiC}_x\text{O}_{4-x}$ -fractions extracted from the ^{29}Si CPMAS NMR spectra of the SiOC-PDCs in Figure 3c).

Si-species in %					
sample	SiO_4	SiCO_3	SiC_2O_2	SiC_4	SiC_3O
SiCO-C14%	25	44	16	5	10
SiCO-C24%	17	28	23	6	25
SiCO-C36%	34	26	14	22	4
SiCO-C55%	19	25	9	42	5

Table S6. Fit data for the Hahn-echo ^{13}C MAS NMR spectra of the SiOC-PDCs with different carbon content shown in the manuscript in Figure 4b).

sample	shift/width	C-species		
		$\text{C}_{\text{sp}2}$	$\text{C}_{\text{sp}2}$	$\text{C}_{\text{sp}3}$
SiCO-C14%	δ (ppm)	139.28	-	23.84
	fwhm (ppm)	76.21	-	83.40
SiCO-C24%	δ (ppm)	137.6	127.46	23.51
	fwhm (ppm)	107.31	31.29	47.7
SiCO-C36%	δ (ppm)	122.32	118.43	-
	fwhm (ppm)	28.24	90.16	-
SiCO-C55%	δ (ppm)	130.66	121.17	-
	fwhm (ppm)	82.13	25.63	-

Table S7. Percentages of the C-fractions achieved from the Hahn-echo ^{13}C MAS NMR spectra of the SiOC-PDCs in Figure 4b).

C-species in %			
sample	$\text{C}_{\text{sp}2}$	$\text{C}_{\text{sp}2}$	$\text{C}_{\text{sp}3}$
SiCO-C14%	52	-	48
SiCO-C24%	35	19	46
SiCO-C36%	6	94	-
SiCO-C55%	87	13	-

Table S8. Fit data for the ^{13}C CPMAS NMR spectra of the SiOC-PDCs with different carbon content shown in the manuscript in Figure 4c).

sample	shift/width	C-species			
		CO-group	$\text{C}_{\text{sp}2}$	CSi_4	$\text{SiC}_x\text{O}_{4-x}$
SiCO-C14%	δ (ppm)	176.08	139.66	15.02	-13.31
	fwhm (ppm)	15	29.50	32.8	42.47
SiCO-C24%	δ (ppm)	175.09	138.9	14.88	-12.85
	fwhm (ppm)	15.25	32	32	57.07
SiCO-C36%	δ (ppm)	173.7	130.4	14.45	-10.65
	fwhm (ppm)	12.26	39	32.44	50.54
SiCO-C55%	δ (ppm)	174.9	131.06	15.34	-13.58
	fwhm (ppm)	17.91	32.72	32.31	30.92

Table S9. Percentages of the C-fractions obtained from the ^{13}C CPMAS NMR spectra of the SiOC-PDCs in Figure 4c).

sample	C-species in %			
	CO-group	C _{sp2}	CSi ₄	SiC _x O _{4-x}
SiCO-C14%	31	28	26	15
SiCO-C24%	29	27	29	15
SiCO-C36%	14	47	13	26
SiCO-C55%	20	56	14	10

Additional NMR spectra

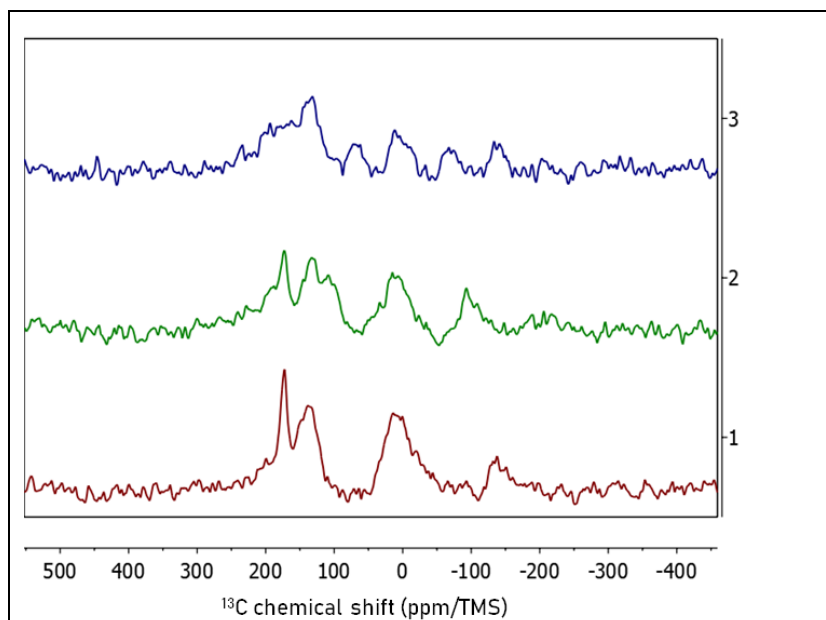
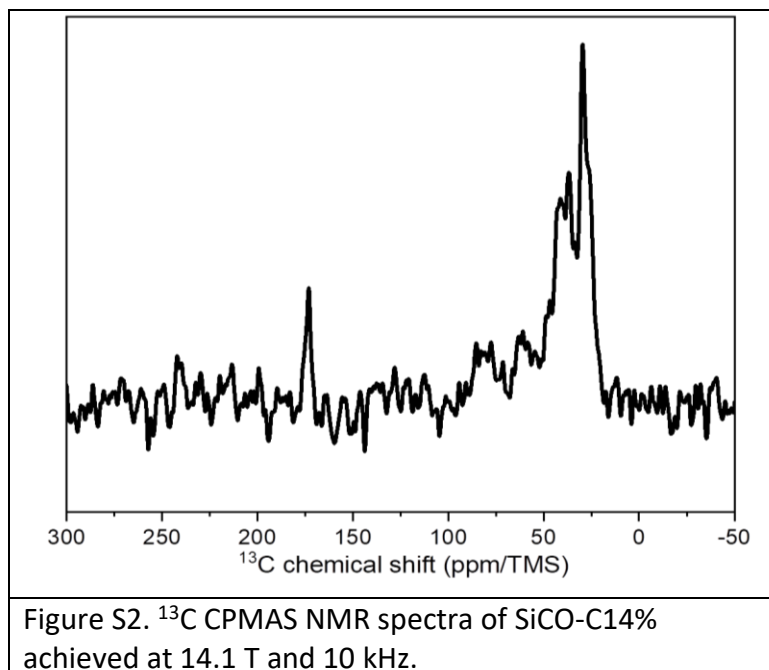


Figure S1. ^{13}C CPMAS NMR spectra of SiCO-C14% collected at 7 T applying the different spinning frequencies of 1) 10 kHz 2) 7 kHz and 3) 5 kHz to inspect the isotropic chemical behavior of the signal at 175 ppm.



Atomistic modelling

Molecular dynamics simulations

Molecular-dynamics (MD) cook-and-quench simulations were performed using LAMMPS [1] in order to prepare amorphous silica and carbon models; the silica models were then used as host matrix for further embedding of C and further optimized using density functional theory calculations (details see below). In all MD simulations an Nose-Hoover thermostat [2,3] and a Parrinello-Rahman barostat [4] was used to control temperature and pressure. A time step of 1 fs, and damping factors of 100 fs (thermostat) and 1000 fs (barostat) were used. For silica, we used the recent Gaussian Approximation Potential (GAP) of Erhard et al. [5], which is capable to generate ideal networks by simple melt quenching. Initially a crystalline structure consisting of 192 atoms was heated to 3000 K, then quenched back to 300 K and finally relaxed at zero K. Four-fold coordinated carbon was now introduced by (i) replacing a Si atom in the silica network with C, (ii) removing all neighboring O, and (iii) displacing all 2nd nearest-neighbor Si atoms towards the inserted C. Thereafter density functional theory (DFT) relaxation are performed for further optimization (computational details, see below). We emphasize that these DFT relaxations must be performed with care to preserve the ideal 4-fold coordination of C and/or Si in the vicinity of

the inserted C. After several attempts we found that compression of the initial (carbonized) structure and slowly releasing the stress (by iteratively increasing the volume isotropically in between atomic relaxations) significantly helps to avoid breaking of bonds during optimization. Eventually (after four to five iterations), a full optimization of the model (keeping the orthogonality of the cell vectors) is performed. Despite this careful construction, still, some of the C-Si bonds break during the relaxation processes, eventually leading to the occurrence of minor defects. Chemical shifts associated with atoms inside such defective environments are not further reported here.

For the disordered carbon model, a classical interatomic potential [6] was used. Various replicas were considered. Each replica consisted of randomly distributed C chains and rings. In more detail, lignin fragments [7], with all non-carbon atoms stripped off were distributed on a regular grid and rotated randomly. The system was heated to 1000 K, then quenched back to 300 K and finally relaxed at zero K. The lowest-energy structure among all replicas was further optimized using DFT calculations. This configuration consists of 72% 3-fold, 23% 4-fold, and 5% 2-fold coordinated carbon.

Electronic structure calculations

The electronic-structure calculations were performed using the projector-augmented plane wave DFT codes GPAW (for optimization) and VASP (for calculating chemical shifts) [8–11]. In both cases, the PBE [12] implementation of the generalized-gradient approximation was used. For all DFT calculations, the energy cut-off was set to 800 eV. Brillouin-zone samplings [13] are listed in Table 1 together with cell dimensions and corresponding k-point densities. We have verified that the calculated chemical shifts are converged within +/- 1 ppm.

Table S10. Lattice parameters, Monkhorst-Pack k-point meshes, and corresponding k-point densities $n_k = N_k * a_k$ for all considered systems. For SiCO, various compositions were considered; we thus give the average lattice parameters.

System	Lattice parameters (Å)			# of k points			K-point density (Å)		
	a ₁	a ₂	a ₃	N ₁	N ₂	N ₃	n ₁	n ₂	n ₃
SiOC	13.353	13.220	13.419	1	1	1	13	13	13
d-C	14.526	9.544	8.430	1	2	2	14.5	19	17
TMS	15.000	15.000	15.000	1	1	1	15	15	15

Chemical shifts

The Tables S11 and S12 summarize the calculated chemical shifts of Si and C in different chemical environments. This data forms the basis of the histograms presented in Figure 2 in the main text.

Table S11. Calculated chemical shifts and standard deviations in ppm for Si in different environments. The degeneracy reflects the number of atoms in a particular bonding environment present in all model systems.

Bond. Env.	degeneracy	Relative to SiO ₄	Relative to TMS	stdev
SiO ₄	1070	0	-103	11
SiCO ₃	161	+ 33	-70	15
SiC ₂ O ₂	32	+ 64	-39	10
SiC ₃ O	9	+ 100	-3	16
SiC ₄	6	+ 93	-10	8

Table S12. Calculated chemical shifts and standard deviations in ppm for C in different environments.

Bond. Env.	degeneracy	Relative to SiC (zincblende)	Relative to TMS (Si(CH ₃) ₄)	stdev
CSi ₄	47	39	80	18
CSi ₂ H ₂	8	-25	16	2
CC ₃	98	112	153	18

CC ₄	31	50	91	15
CSi ₃	98	36	77	38
CC ₂	7	155	196	43

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